

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM1G43,SM1J43

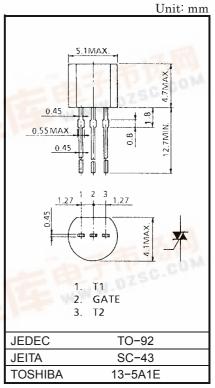
### AC POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage : V<sub>DRM</sub> = 400, 600V
 R.M.S On-State Current : I<sub>T</sub> (RMS) = 1A

• Higt Commutating (dv / dt)

#### **MAXIMUM RATINGS**

| CHARACTER                                       | ISTIC      | SYMBOL               | RATING     | UNIT             |  |
|---|------------|----------------------|------------|------------------|--|
| Repetitive Peak<br>Off-State Voltage            | SM1G43     | V <sub>DRM</sub>     | 400        | V                |  |
|   | SM1J43     | ▼DRM                 | 600        |                  |  |
| R.M.S On-State Currer<br>(Full Sine Waveform To |            | I <sub>T (RMS)</sub> | 1.0        | А                |  |
| Peak One Cycle Surge                            | On-State   | l=                   | 8 (50Hz)   | Α                |  |
| Current (Non-Repetitive)                        |            | ITSM                 | 8.8 (60Hz) | A                |  |
| I <sup>2</sup> t Limit Value                    |            | I <sup>2</sup> t     | 0.32       | A <sup>2</sup> s |  |
| Peak Gate Power Dissi                           | pation     | P <sub>GM</sub>      | 10 M 1     | W                |  |
| Average Gate Power D                            | issipation | P <sub>G (AV)</sub>  | 0.1        | W                |  |
| Peak Gate Voltage                               | The Art.   | V <sub>GM</sub>      | 6          | V                |  |
| Peak Gate Current                               |            | I <sub>GM</sub>      | 0.5        | А                |  |
| Junction Temperature                            |            | Tj                   | -40~125    | °C               |  |
| Storage Temperature F                           | Range      | T <sub>stg</sub>     | -40~125    | °C               |  |



Weight: 0.2g

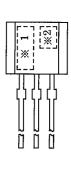


# **TOSHIBA**

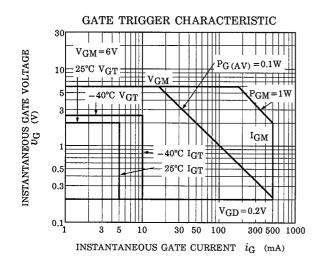
## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

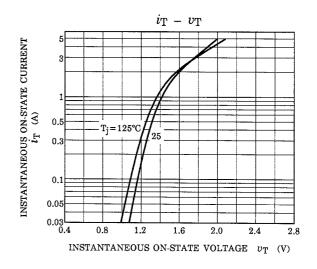
| CHARACTERISTIC                    |     | SYMBOL                | TEST CONDITION                                |                   | MIN | TYP. | MAX | UNIT |
|-----------------------------------|-----|-----------------------|---|-------------------|-----|------|-----|------|
| Repetitive Peak Off-State Current |     | I <sub>DRM</sub>      | V <sub>DRM</sub> = Rated                      |                   | _   | _    | 10  | μΑ   |
| Gate Trigger Voltage              | I   | V <sub>GT</sub>       | $V_D = 12V$ , $R_L = 20\Omega$                | T2 (+), Gate (+)  | _   | _    | 2   | · V  |
|                                   | П   |                       |   | T2 (+) , Gate (-) | _   | _    | 2   |      |
|                                   | III |                       |   | T2 (-) , Gate (-) | _   | _    | 2   |      |
|                                   | IV  |                       |   | T2 (-) , Gate (+) | _   | 2    | _   |      |
| Gate Trigger Current              | I   | I <sub>GT</sub>       | V <sub>D</sub> = 12V,<br>R <sub>L</sub> = 20Ω | T2 (+), Gate (+)  | _   | _    | 5   | - mA |
|                                   | П   |                       |   | T2 (+) , Gate (−) | _   | _    | 5   |      |
|                                   | III |                       |   | T2 (-) , Gate (-) | _   | _    | 5   |      |
|                                   | IV  |                       |   | T2 (-) , Gate (+) | _   | 10   | _   |      |
| Peak On-State Voltage             |     | V <sub>TM</sub>       | I <sub>TM</sub> = 1.5A                        |                   | _   | _    | 1.5 | V    |
| Gate Non-Trigger Voltage          |     | $V_{GD}$              | V <sub>D</sub> = Rated, Tc = 125°C            |                   | 0.2 | _    | _   | V    |
| Holding Current                   |     | lΗ                    | V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A    |                   | _   | _    | 10  | mA   |
| Thermal Resistance                |     | R <sub>th (j−c)</sub> | Junction to Case, AC                          |                   | _   | _    | 40  | °C/W |
| Thermal Resistance                |     | R <sub>th (j−a)</sub> | Junction to Ambient, AC                       |                   | _   | _    | 180 | °C/W |

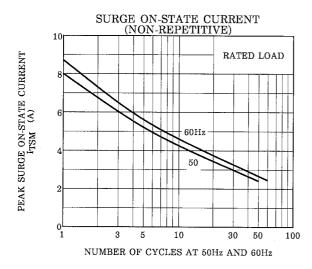
### **MARKING**

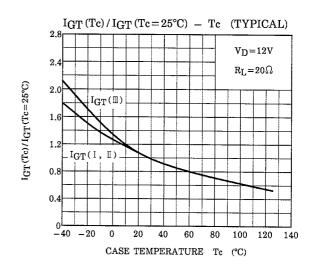


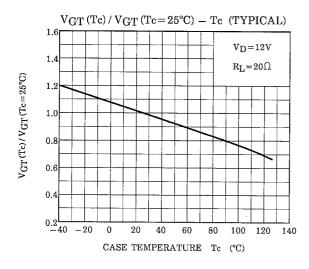
| NUMBER |  | SYMBOL | MARK   |  |  |
|--------|--|--------|--|--|--|
| *1     | TYPE   | SM1G43 | M1G43  |  |  |
|        | IIFL   | SM1J43 | M1J43  |  |  |
| *2     | Lot Number  Month (Starting from Alphabet A)  Year (Last Decimal Digit of the Current Year ) |        | Example<br>8A : January 1998<br>8B : February 1998<br>8L : December 1998 |  |  |

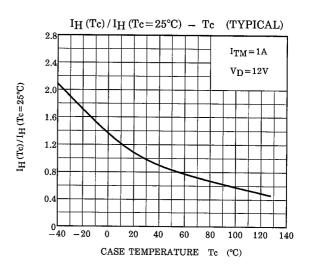




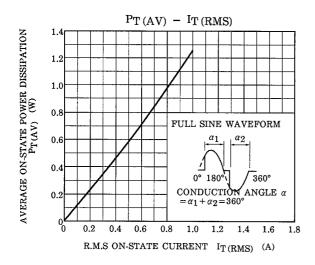


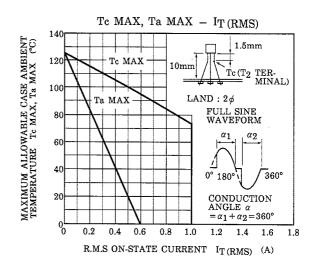


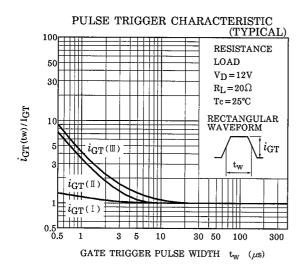


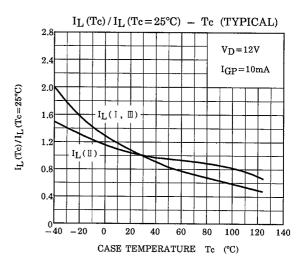


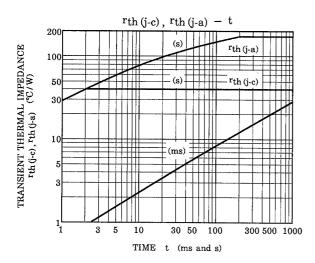
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